

Supporting Information

Ammonia decomposition mediated at nitrogen vacancy on NaCl-type binary metal nitride supported with transition metal nanoparticles

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1. Experimental

1.1. Sample preparation

The LaN and CeN were synthesized by the nitridation of LaH₃ and CeH₃ as previously reported in the literature.¹ The LaH₃ and CeH₃ were, in turn, prepared by hydrogenation of pieces of La and Ce metal (99.9%, Rare Metallic Co.) under 1.5 MPa of H₂ gas at room temperature for 2 h. LaN and CeN were subsequently prepared from the hydride powders by heating at 600 °C under a N₂ gas flow (10 mL·min⁻¹) for 12 h. Other nitride materials (YN, ZrN, and HfN) were purchased from the Kojundo Chemical Laboratory. CeN with high surface area (CeN-HS) was synthesized via nitridation of a CeH₂ nanopowder made by an arc-evaporation method as previously reported.² Nickel-supported catalysts were synthesized by H₂ reduction reactions of mixtures of Ni(η -C₅H₅)₂ (98.0%, Tokyo Chemical Industry) and various support materials at 250 °C for 1.5 h.

1.2. Catalytic reactions

Each ammonia decomposition reaction was conducted in a fixed-bed plug-flow silica glass tube reactor at ambient pressure. Each of the prepared catalysts was pretreated by heating under a N₂/H₂ mixed gas flow (N₂:H₂=1:3, 20 mL·min⁻¹) at 500 °C for 1 h. Catalytic performance and stability tests were conducted using 0.1 g catalyst specimens over the range of 360–660 °C in a stream of pure NH₃ gas (25 mL·min⁻¹), corresponding to a weight hourly space velocity (WHSV) of 15,000 mL_{NH₃}·g⁻¹·h⁻¹. Effluent gases were analyzed with an online gas chromatograph (GC-14A, incorporating a thermal conductivity detector and Porapak OS column, Shimadzu, with He as the carrier gas). The NH₃ conversion was calculated as

$$X_{NH_3} = \frac{C_{NH_3, 0} - C_{NH_3}}{C_{NH_3, 0} + C_{NH_3}} \quad (1)$$

Where $C_{NH_3, 0}$ is the concentration of NH₃ in the inlet gas and C_{NH_3} is the concentration in the outlet gas. Trials involving ¹⁵N-labeled NH₃ gas decomposition were performed at 500 °C over both the Ni/CeN and CeN specimens in a U-shaped quartz glass reactor connected to a closed gas

circulation system. These experiments each employed 75 mg of the catalyst and introduced 4.0 mmol $^{15}\text{NH}_3$ (98% isotopic purity).

1.3. Characterization

The crystal structures of the catalysts were examined by acquiring powder X-ray diffraction (XRD) patterns (D2 PHASER, Bruker) employing Cu K α radiation. To prevent the air exposure of the unstable nitrides (LaN, CeN, and YN), we employed the Ar-sealed XRD holder, which has a broad amorphous diffraction below $\theta = 25^\circ$. H $_2$ -TPD and N $_2$ -TPD analyses were conducted using a BELCAT-A apparatus (MicrotracBEL, Japan). Ni K-edge X-ray adsorption fine structure (XAFS) data were obtained using the synchrotron radiation ring at the PF-12C beamline of the KEK Photon Factory with Si(111) single-crystal monochromators. Brunauer–Emmett–Teller (BET) surface areas were calculated based on N $_2$ adsorption–desorption isotherms acquired at 77 K using a BELSORP-mini II apparatus (MicrotracBEL).

1.4. Density functional theory calculations

Periodic density functional theory (DFT) calculations based on slab models were performed using the Vienna Ab Initio Simulation Package (VASP) code³ with the Perdew–Burke–Ernzerhof exchange–correlation functional⁴ based on the projector augmented wave (PAW) method.^{5,6} The plane-wave basis set was truncated at a kinetic energy of 500 eV and a Monkhorst-Pack k-point grid separation⁷ for the Brillouin zone sampling was $3 \times 3 \times 1$ for each surface models. The convergence criteria for structural optimization and energy calculations comprised an SCF tolerance of 1.0×10^{-6} eV per atom, an energy tolerance of 5.0×10^{-5} eV per atom and a maximum force tolerance of $0.05 \text{ eV} \cdot \text{\AA}^{-1}$. The DFT + U method (DFT plus Hubbard-U parameter) was employed for all DFT calculations.⁸ The effective Hubbard-U parameter, that is, $U - J$, was set to 7.0 eV (Ce) and 4.0 eV (La). The formation Energy of N $^{3-}$ vacancies on each nitride surface was defined as

$$E_f(V_N) = \{E(S^d) + 0.5 \times E(N_2)\} - E(S^p)$$

Where $E(A)$ represents the total energy of system A and S^d and S^p represent Nitrides and without surface V_N , respectively.

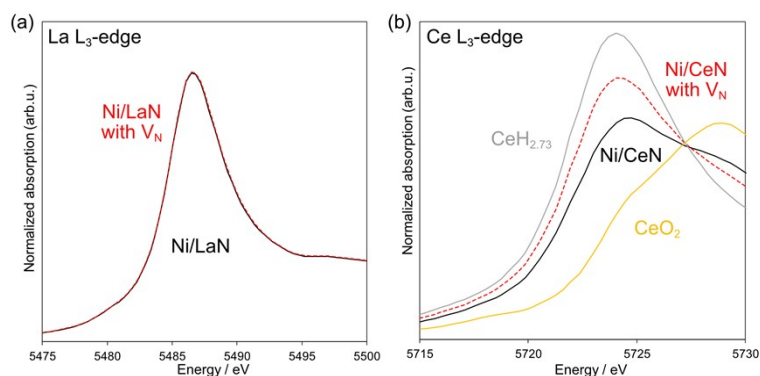
Table

Table S1. Specific surface area of nitrides.

Nitrides	Specific surface area ($\text{m}^2 \cdot \text{g}^{-1}$)
CeN	3.5
CeN-HS	23.1
LaN	1.9
YN	4.0
ZrN	1.0
HfN	0.1

Table S2. Summary of previously reported Ni-supported catalyst for ammonia decomposition.

Catalysts	Ni content (wt%)	T ($^{\circ}\text{C}$)	WHSV ($\text{mLg}_{\text{cat}}^{-1}\text{h}^{-1}$)	Conversion (%)	H_2 production rate ($\text{mmol}_{\text{H}_2\text{g}_{\text{cat}}^{-1}\text{min}^{-1}}$)	H_2 production rate ($\text{mmol}_{\text{H}_2\text{g}_{\text{Ni}}^{-1}\text{min}^{-1}}$)	Ref.
Ni/CeN-HS	10	500	15000	86.4	14.5	144.6	This work
Ni/CeN	5	500	15000	51.2	8.6	171.4	This work
Ni/LaN	5	500	15000	39.3	6.6	131.6	This work
Ni/YN	5	500	15000	16.7	2.8	55.9	This work
Ni/ZrN	5	500	15000	5.2	0.9	17.4	This work
Ni/HfN	5	500	15000	0.9	0.2	3	This work
NaNH_2 -Ni-GNP	8	500	60000	-	13.9	173.4	9
Ce-Ni/ Al_2O_3	43.4	500	30000	71.9	24.1	55.5	10
La-Ni/ Al_2O_3	37.9	500	30000	63.9	21.4	56.5	11
Ni/SBA-15	23.4	500	30000	57	19.1	81.6	12
Ni/MCM-41	7.2	500	30000	26.9	9	125.1	13
Ni/ SiO_2	10	500	30000	10.5	3.5	35.2	14
Ni/CNT	2.9	500	30000	9	3	103.9	15
Ni-Ce-Al-O microsphere	-	500	18000	88	17.7	-	16
Ni/h-Ba $\text{TiO}_{3-x}\text{N}_y$	5	500	15000	58	9.7	194.3	17
Ni/CaNH-HS	10	500	15000	91.2	15.3	152.7	18
Ni/ Al_2O_3	10	500	15000	20	3.3	33.5	18
Ni/CaO	10	500	15000	16	2.7	26.8	18
Ni/C12A7:e- Ni doped	7.4	500	15000	13.3	2.2	30.1	18
LiNH_2/C	5	400	13000	53	7.7	153.8	19



Figures

Figure S1. XANES spectra before and after introduction of V_N for (a) Ni/LaN and (b) Ni/CeN with the references. CeH_{2.73} was prepared by the hydrogenation of metal Ce under 1 MPa H₂ at room temperature. The chemical composition of prepared hydride was determined to be CeH_{2.73} by the XRD patterns in previous study.²⁰

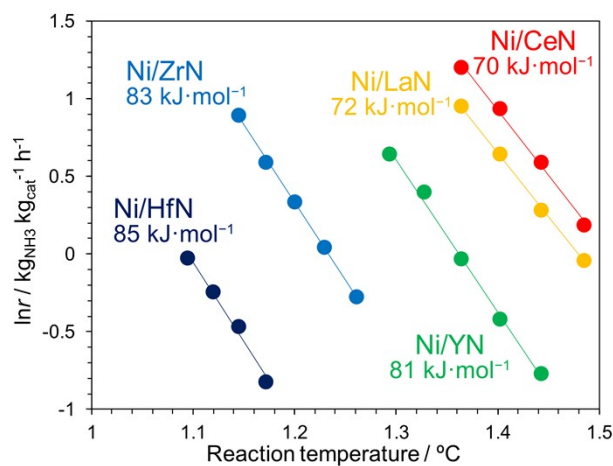


Figure S2. Arrhenius plots for ammonia decomposition over Ni/TMN (TM = La, Ce, Y, Zr or Hf) below 30% NH₃ conversion.

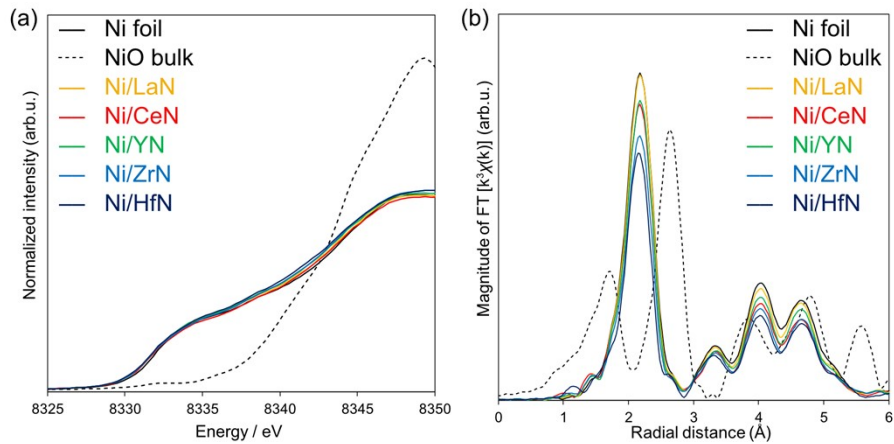


Figure S3. (a) Ni K-edge XANES spectra of Ni/nitrides along with Ni and NiO as references. (b) Fourier transform of k^3 -weighted EXAFS oscillations for Ni/nitrides along with those for Ni and NiO.

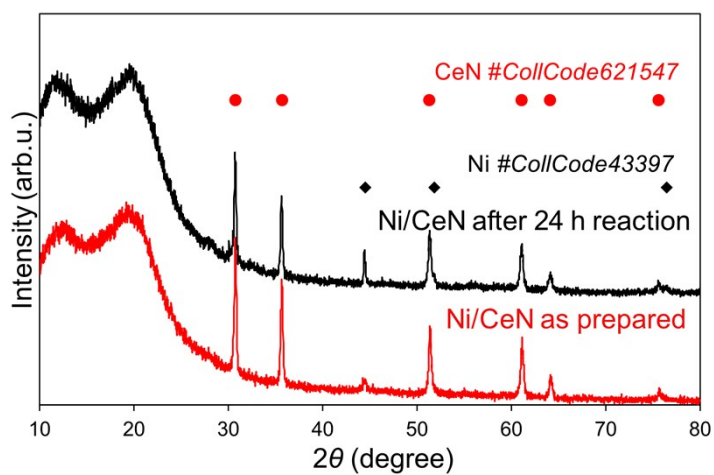


Figure S4. XRD patterns for 10 wt% Ni/CeN as prepared and after 24 h ammonia decomposition reaction at 500°C .

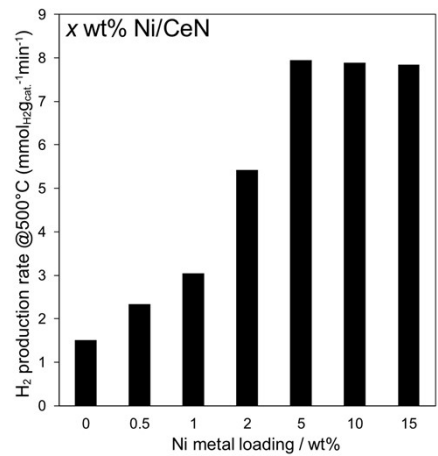


Figure S5. Hydrogen production rate obtained with CeN specimens having various Ni loadings.

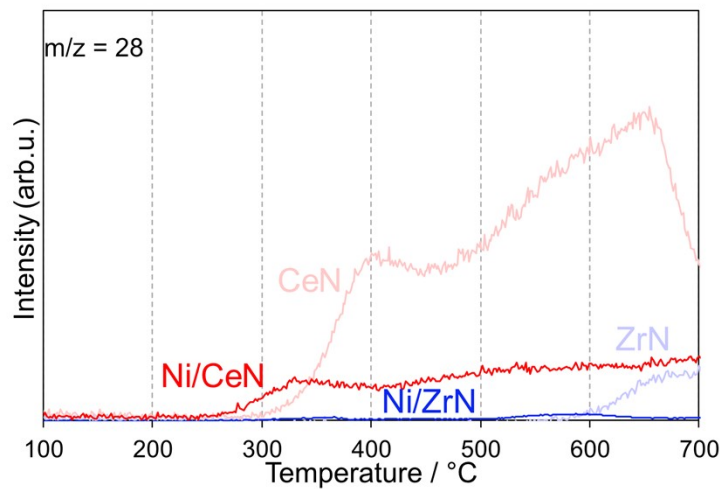


Figure S6. TPD profiles for Ni/CeN and Ni/ZrN under He flow based on monitoring at $m/z = 28$.

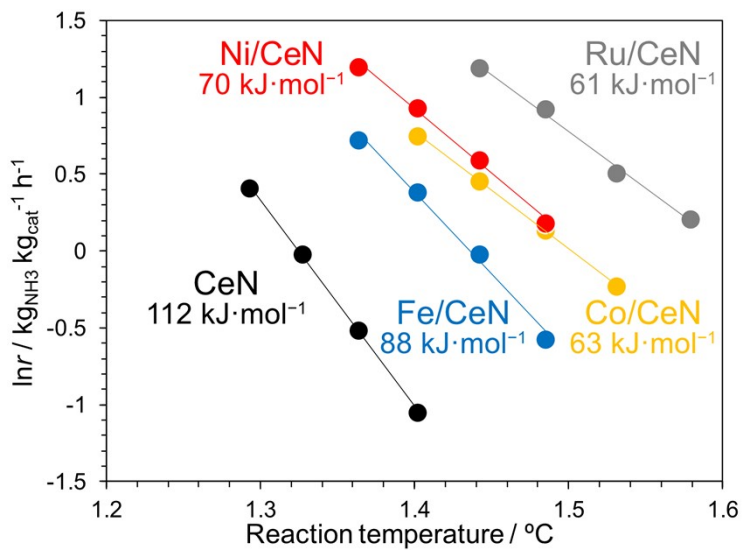


Figure S7. Arrhenius plots for ammonia decomposition over M/CeN (M = Ru, Ni, Co or Fe) below 30% NH₃ conversion.

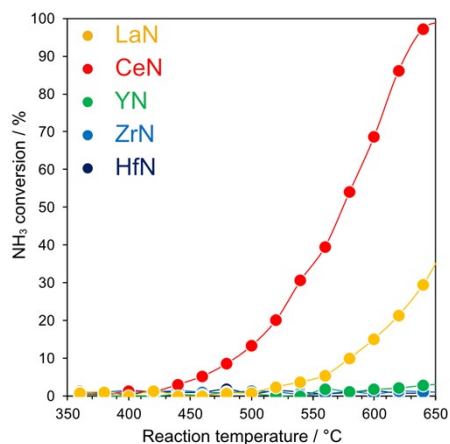


Figure S8. NH_3 conversion during ammonia decomposition over nitrides without metal loading as function of temperature.

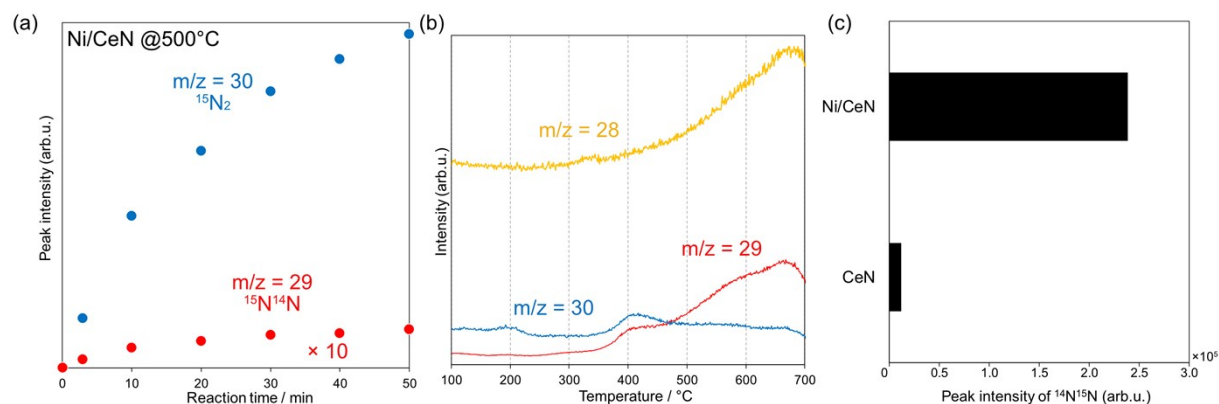


Figure S9. (a) Data from $^{15}\text{NH}_3$ decomposition trial using Ni/CeN at 500 °C. (b) N_2 -TPD profiles for Ni/CeN after the $^{15}\text{NH}_3$ decomposition trial at 500 °C. (c) $^{14}\text{N}^{15}\text{N}$ produced over 30 min during initial state of $^{15}\text{NH}_3$ decomposition over Ni/CeN and CeN.

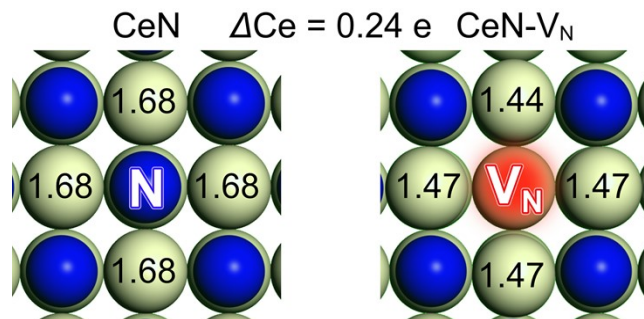


Figure S10. Bader charge analysis of nitride surfaces with V_N formation on CeN (001).

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